

TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type

SSM3J112TU

High Speed Switching Applications

- 4V drive
- Low on-resistance: $R_{on} = 790\text{m}\Omega$ (max) (@ $V_{GS} = -4\text{ V}$)
 $R_{on} = 390\text{m}\Omega$ (max) (@ $V_{GS} = -10\text{ V}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	-30	V
Gate-Source voltage	V_{GSS}	± 20	V
Drain current	DC	I_D	-1.1
	Pulse	I_{DP}	-2.2
Drain power dissipation	P_D (Note 1)	800	mW
	P_D (Note 2)	500	
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

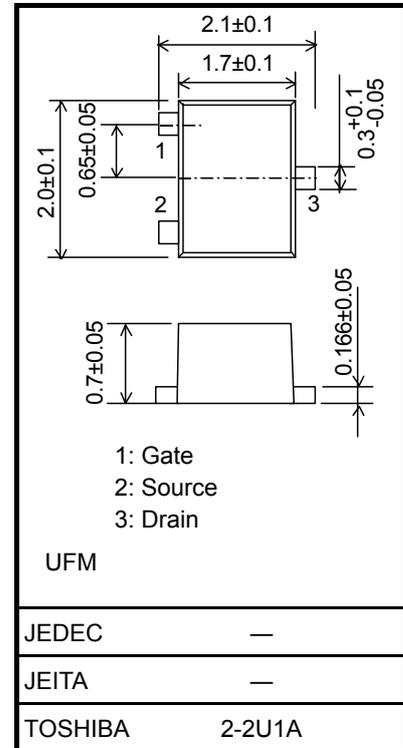
- Note 1: Mounted on ceramic board.
 (25.4 mm × 25.4 mm × 0.8 mm, Cu Pad: 645 mm²)
- Note 2: Mounted on FR4 board.
 (25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm²)

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1\text{ mA}, V_{GS} = 0$	-30	—	—	V
	$V_{(BR)DSX}$	$I_D = -1\text{ mA}, V_{GS} = +20\text{ V}$	-15	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0$	—	—	-1	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0$	—	—	± 1	μA
Gate threshold voltage	V_{th}	$V_{DS} = -5\text{ V}, I_D = -0.1\text{ mA}$	-0.8	—	-1.8	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -5\text{ V}, I_D = -0.5\text{ A}$ (Note3)	0.5	1.0	—	S
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = -0.5\text{ A}, V_{GS} = -10\text{ V}$ (Note3)	—	310	390	mΩ
		$I_D = -0.5\text{ A}, V_{GS} = -4\text{ V}$ (Note3)	—	610	790	
Input capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	86	—	pF
Output capacitance	C_{oss}	$V_{DS} = -15\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	25	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = -15\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	14	—	pF
Switching time	Turn-on time	$V_{DD} = -15\text{ V}, I_D = -0.5\text{ A},$ $V_{GS} = 0 \sim -4\text{ V}, R_G = 10\ \Omega$	—	14	—	ns
	Turn-off time		—	8.5	—	
Drain-Source forward voltage	V_{DSF}	$I_D = 1.1\text{ A}, V_{GS} = 0\text{ V}$ (Note3)	—	0.85	1.2	V

Note3: Pulse test

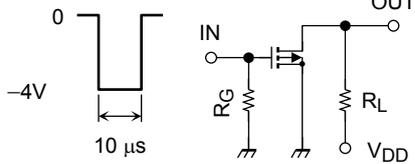
Unit: mm



Weight: 6.6 mg (typ.)

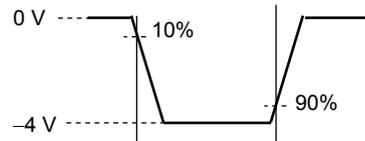
Switching Time Test Circuit

(a) Test circuit

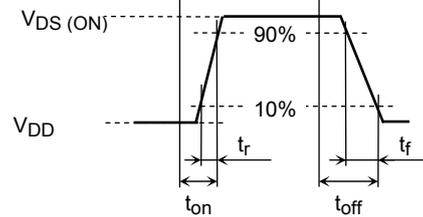


$V_{DD} = -10\text{ V}$
 $R_G = 4.7\ \Omega$
 $D.U. \leq 1\%$
 $V_{IN}: t_r, t_f < 5\text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

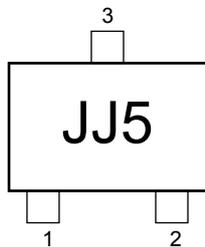
(b) V_{IN}



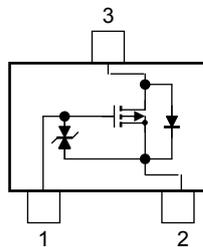
(c) V_{OUT}



Marking



Equivalent Circuit (top view)



Precaution

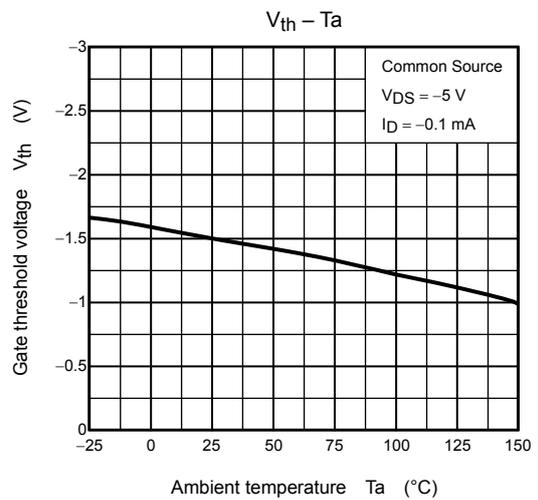
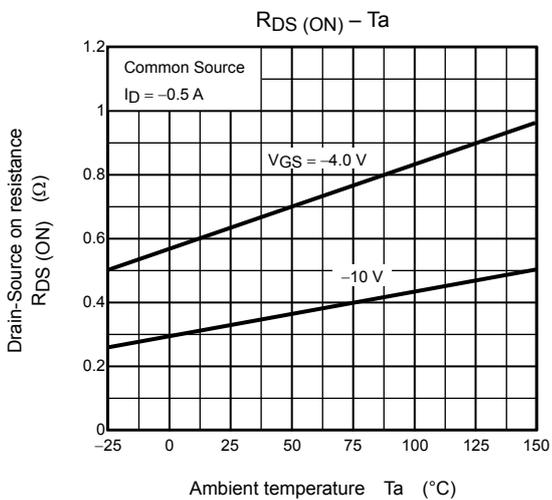
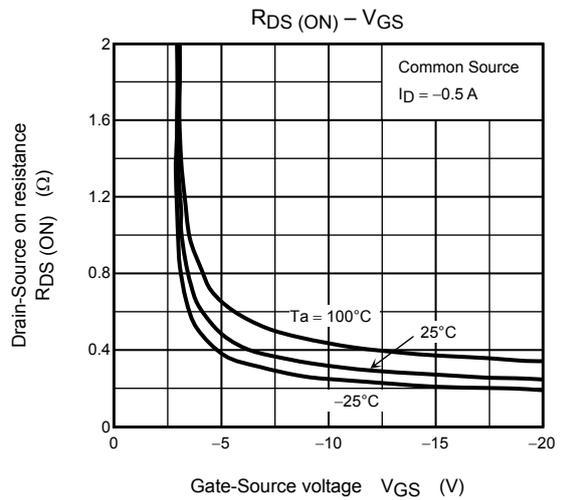
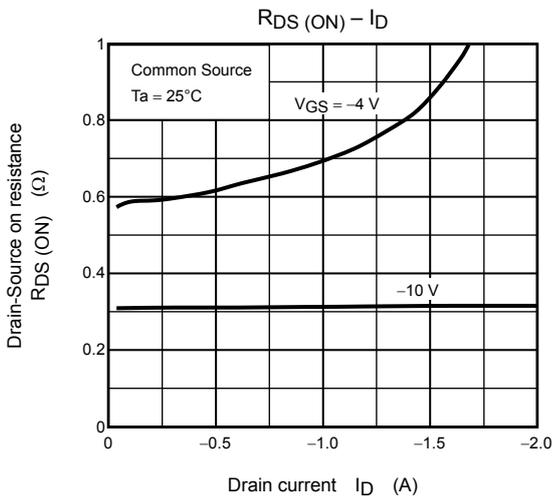
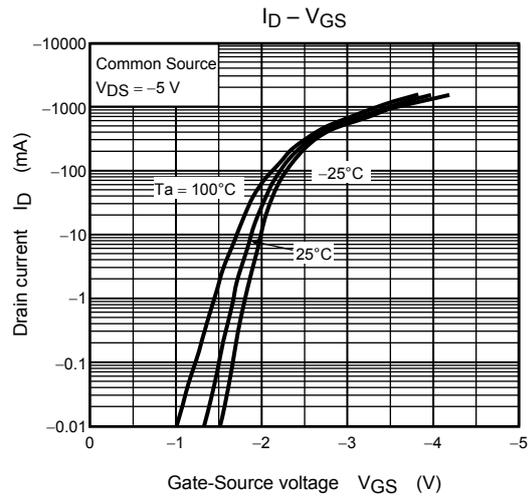
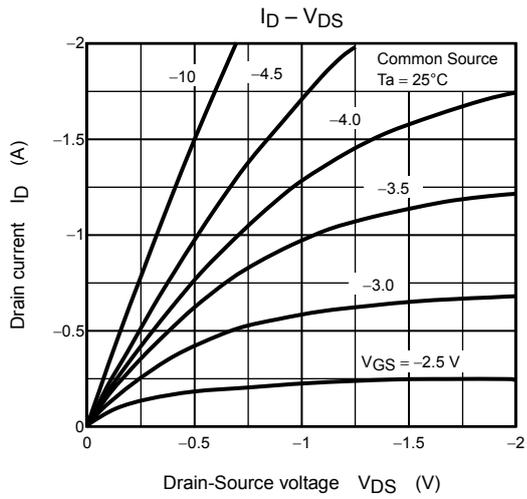
V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = -0.1\text{ mA}$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} , and $V_{GS(off)}$ requires a lower voltage than V_{th} .

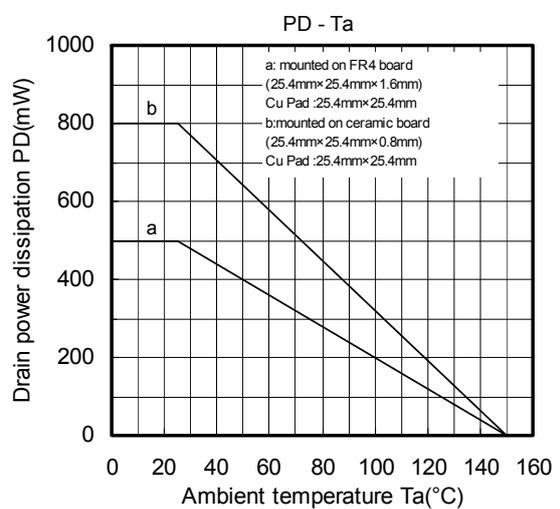
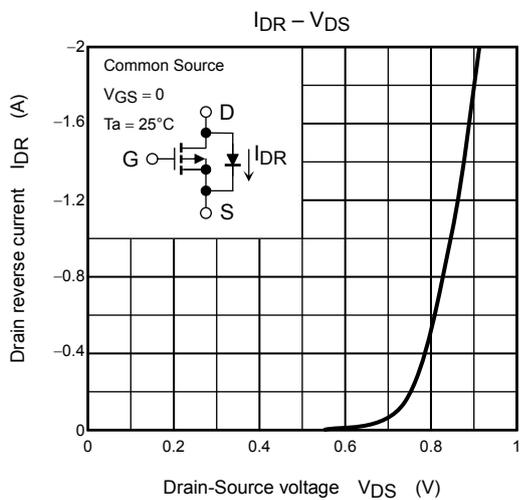
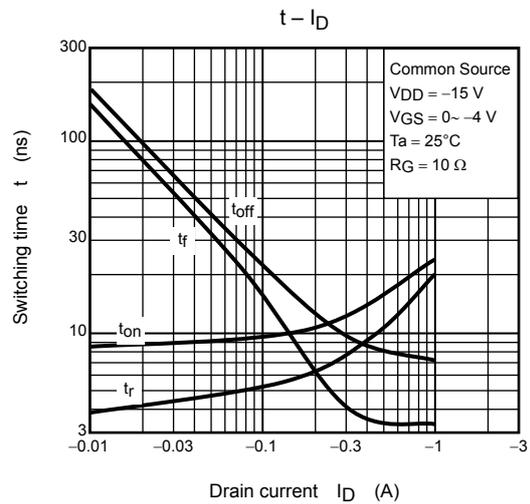
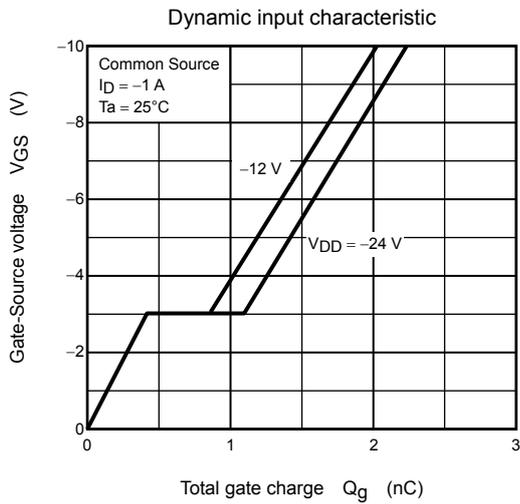
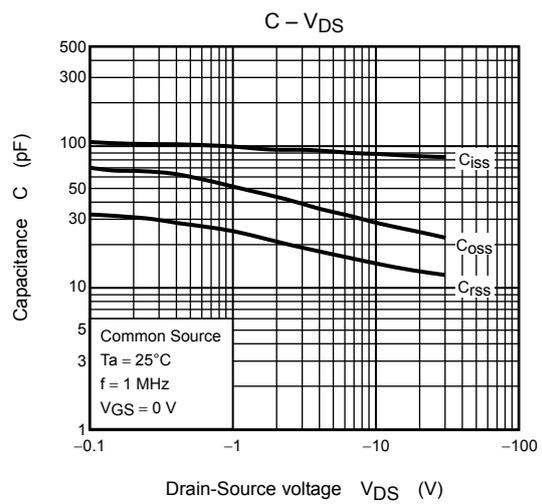
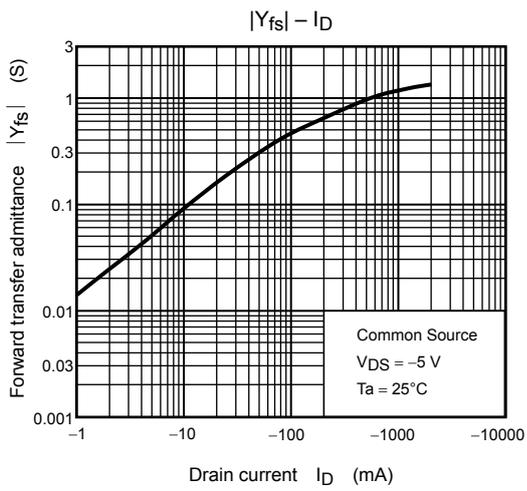
(The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$)

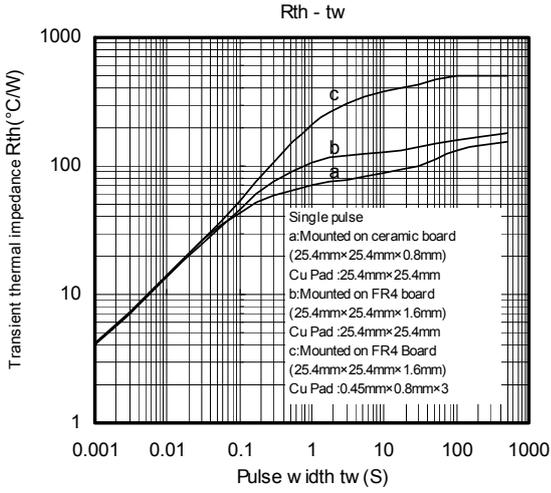
Take this into consideration when using the device.

Handling Precaution

When handling individual devices which are not yet mounted on a circuit board, be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.







RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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